

Fei Zhuge

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75
papers

3,069
citations

32
h-index

54
g-index

79
ext. papers

3,430
ext. citations

5.2
avg, IF

4.96
L-index

#	Paper	IF	Citations
75	p-type conduction in NAl co-doped ZnO thin films. <i>Applied Physics Letters</i> , 2004 , 85, 3134-3135	3.4	208
74	Nonvolatile resistive switching in graphene oxide thin films. <i>Applied Physics Letters</i> , 2009 , 95, 232101	3.4	192
73	Resistance switching in polycrystalline BiFeO ₃ thin films. <i>Applied Physics Letters</i> , 2010 , 97, 042101	3.4	129
72	Ultrasensitive Memristive Synapses Based on Lightly Oxidized Sulfide Films. <i>Advanced Materials</i> , 2017 , 29, 1606927	24	127
71	Effect of top electrodes on photovoltaic properties of polycrystalline BiFeO ₃ based thin film capacitors. <i>Nanotechnology</i> , 2011 , 22, 195201	3.4	127
70	Mechanism of nonvolatile resistive switching in graphene oxide thin films. <i>Carbon</i> , 2011 , 49, 3796-3802	10.4	124
69	Nonvolatile resistive switching memory based on amorphous carbon. <i>Applied Physics Letters</i> , 2010 , 96, 163505	3.4	123
68	Mechanism for resistive switching in an oxide-based electrochemical metallization memory. <i>Applied Physics Letters</i> , 2012 , 100, 072101	3.4	107
67	Nonvolatile resistive switching in metal/La-doped BiFeO ₃ /Pt sandwiches. <i>Nanotechnology</i> , 2010 , 21, 425202	3.4	94
66	Structural, chemical, optical, and electrical evolution of SnO(x) films deposited by reactive rf magnetron sputtering. <i>ACS Applied Materials & Interfaces</i> , 2012 , 4, 5673-7	9.5	93
65	Improvement of resistive switching in Cu/ZnO/Pt sandwiches by weakening the randomness of the formation/rupture of Cu filaments. <i>Nanotechnology</i> , 2011 , 22, 275204	3.4	91
64	ZnO p-n homojunctions and ohmic contacts to AlN-co-doped p-type ZnO. <i>Applied Physics Letters</i> , 2005 , 87, 092103	3.4	86
63	Strain and its effect on optical properties of Al-N codoped ZnO films. <i>Journal of Applied Physics</i> , 2006 , 99, 023503	2.5	86
62	High-temperature tolerance in WTi-Al ₂ O ₃ cermet-based solar selective absorbing coatings with low thermal emissivity. <i>Nano Energy</i> , 2017 , 37, 232-241	17.1	84
61	Ambipolar inverters using SnO thin-film transistors with balanced electron and hole mobilities. <i>Applied Physics Letters</i> , 2012 , 100, 263502	3.4	72
60	Nonvolatile bistable resistive switching in a new polyimide bearing 9-phenyl-9H-carbazole pendant. <i>Journal of Materials Chemistry</i> , 2012 , 22, 520-526		69
59	Improvement of reproducible resistance switching in polycrystalline tungsten oxide films by in situ oxygen annealing. <i>Applied Physics Letters</i> , 2010 , 96, 072103	3.4	68

58	ZnO light-emitting diodes fabricated on Si substrates with homobuffer layers. <i>Applied Physics Letters</i> , 2007 , 91, 113503	3.4	67
57	Synaptic devices based on purely electronic memristors. <i>Applied Physics Letters</i> , 2016 , 108, 013504	3.4	52
56	Electrical characterization of ZnO-based homojunctions. <i>Applied Physics Letters</i> , 2006 , 89, 053501	3.4	51
55	Optoelectronic neuromorphic thin-film transistors capable of selective attention and with ultra-low power dissipation. <i>Nano Energy</i> , 2019 , 62, 772-780	17.1	48
54	Semiconducting ZnSnN ₂ thin films for Si/ZnSnN ₂ p-n junctions. <i>Applied Physics Letters</i> , 2016 , 108, 142104	3.4	44
53	Determination of some basic physical parameters of SnO based on SnO/Si pn heterojunctions. <i>Applied Physics Letters</i> , 2015 , 106, 132102	3.4	43
52	Mechanism for resistive switching in chalcogenide-based electrochemical metallization memory cells. <i>AIP Advances</i> , 2015 , 5, 057125	1.5	41
51	Microstructure dependence of leakage and resistive switching behaviours in Ce-doped BiFeO ₃ thin films. <i>Journal Physics D: Applied Physics</i> , 2011 , 44, 415104	3	40
50	Roles of silver oxide in the bipolar resistance switching devices with silver electrode. <i>Applied Physics Letters</i> , 2011 , 98, 072107	3.4	39
49	Rapid synthesis and photoluminescence of novel ZnO nanotetrapods. <i>Journal of Crystal Growth</i> , 2005 , 274, 447-452	1.6	38
48	Memristive Synapses for Brain-Inspired Computing. <i>Advanced Materials Technologies</i> , 2019 , 4, 1800544	6.8	37
47	Formation of quasi-aligned ZnCdO nanorods and nanoneedles. <i>Journal of Crystal Growth</i> , 2005 , 283, 373-377	3.7	37
46	All-Optically Controlled Memristor for Optoelectronic Neuromorphic Computing. <i>Advanced Functional Materials</i> , 2021 , 31, 2005582	15.6	34
45	Electrically controlled electron transfer and resistance switching in reduced graphene oxide noncovalently functionalized with thionine. <i>Journal of Materials Chemistry</i> , 2012 , 22, 16422		33
44	Template-Free Growth of Well-Ordered Silver Nano Forest/Ceramic Metamaterial Films with Tunable Optical Responses. <i>Advanced Materials</i> , 2017 , 29, 1605324	24	32
43	Substrate biasing effect on the physical properties of reactive RF-magnetron-sputtered aluminum oxide dielectric films on ITO glasses. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 2255-61	9.5	30
42	Electrochromism of Nanocrystal-in-Glass Tungsten Oxide Thin Films under Various Conduction Cations. <i>Inorganic Chemistry</i> , 2019 , 58, 2089-2098	5.1	29
41	Photonic Synapses for Ultrahigh-Speed Neuromorphic Computing. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900082	2.5	28

40	Band Offset Engineering in ZnSnN ₂ -Based Heterojunction for Low-Cost Solar Cells. <i>ACS Photonics</i> , 2018 , 5, 2094-2099	6.3	25
39	p-type ZnO films by codoping of nitrogen and aluminum and ZnO-based p-n homojunctions. <i>Journal of Crystal Growth</i> , 2005 , 283, 413-417	1.6	24
38	Silver nanoparticles with an armor layer embedded in the alumina matrix to form nanocermet thin films with sound thermal stability. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 11550-7	9.5	23
37	Nanocomposite W _{0.5} ThO ₂ thermionic cathode. <i>Materials Letters</i> , 2003 , 57, 2776-2779	3.3	23
36	Thin Film Solar Cell Based on ZnSnN ₂ /SnO Heterojunction. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018 , 12, 1700332	2.5	22
35	Improved N-Al codoped p-type ZnO thin films by introduction of a homo-buffer layer. <i>Journal of Crystal Growth</i> , 2005 , 274, 425-429	1.6	20
34	Plasmonic AgAl Bimetallic Alloy Nanoparticle/Al ₂ O ₃ Nanocermet Thin Films with Robust Thermal Stability for Solar Thermal Applications. <i>Advanced Materials Interfaces</i> , 2016 , 3, 1600248	4.6	20
33	Dependence of properties of N-Al codoped p-type ZnO thin films on growth temperature. <i>Applied Surface Science</i> , 2005 , 245, 109-113	6.7	19
32	Flexible Electrochromic V ₂ O ₅ Thin Films with Ultrahigh Coloration Efficiency on Graphene Electrodes. <i>Journal of the Electrochemical Society</i> , 2018 , 165, D183-D189	3.9	18
31	Single-crystalline metal filament-based resistive switching in a nitrogen-doped carbon film containing conical nanopores. <i>Applied Physics Letters</i> , 2015 , 106, 083104	3.4	17
30	Effects of growth ambient on electrical properties of Al-N co-doped p-type ZnO films. <i>Thin Solid Films</i> , 2005 , 476, 272-275	2.2	17
29	Forming-free resistive switching in a nanoporous nitrogen-doped carbon thin film with ready-made metal nanofilaments. <i>Carbon</i> , 2014 , 76, 459-463	10.4	16
28	Al concentration dependence of electrical and photoluminescent properties of co-doped ZnO films. <i>Chemical Physics Letters</i> , 2007 , 437, 203-206	2.5	16
27	Control of ZnO nanowire growth and optical properties in a vapor deposition process. <i>Journal of Materials Science and Technology</i> , 2017 , 33, 850-855	9.1	15
26	The electrical properties of n-ZnO/p-SnO heterojunction diodes. <i>Applied Physics Letters</i> , 2016 , 109, 123507	9.4	15
25	Carrier localization in codoped ZnO:N:Al films. <i>Solid State Communications</i> , 2006 , 138, 542-545	1.6	14
24	Reproducibility and stability of N-Al codoped p-type ZnO thin films. <i>Journal of Materials Science</i> , 2006 , 41, 467-470	4.3	14
23	Anomalous rectification in a purely electronic memristor. <i>Applied Physics Letters</i> , 2016 , 109, 143505	3.4	14

22	Effect of post-annealing on structural and electrochromic properties of Mo-doped V2O5 thin films. <i>Journal of Sol-Gel Science and Technology</i> , 2016 , 77, 604-609	2.3	13
21	Defect-related vibrational and photoluminescence spectroscopy of a codoped ZnO : Al : N film. <i>Journal Physics D: Applied Physics</i> , 2006 , 39, 2339-2342	3	13
20	AlN codoping and p-type conductivity in ZnO using different nitrogen sources. <i>Surface and Coatings Technology</i> , 2005 , 198, 354-356	4.4	13
19	Memristors based on amorphous ZnSnO films. <i>Materials Letters</i> , 2019 , 249, 169-172	3.3	10
18	Ultralow operation voltages of a transparent memristor based on bilayer ITO. <i>Applied Physics Letters</i> , 2020 , 116, 221602	3.4	10
17	Broadband Optoelectronic Synaptic Thin-Film Transistors Based on Oxide Semiconductors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900630	2.5	10
16	Combined control of the cation and anion to make ZnSnON thin films for visible-light phototransistors with high responsivity. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 6480-6487	7.1	7
15	Broadband hyperbolic metamaterial covering the whole visible-light region. <i>Optics Letters</i> , 2019 , 44, 2970-2973	3	7
14	Hybrid oxide brain-inspired neuromorphic devices for hardware implementation of artificial intelligence. <i>Science and Technology of Advanced Materials</i> , 2021 , 22, 326-344	7.1	7
13	Retina-Inspired Two-Terminal Optoelectronic Neuromorphic Devices with Light-Tunable Short-Term Plasticity for Self-Adjusting Sensing. <i>Advanced Intelligent Systems</i> , 2020 , 2, 2200019	6	7
12	Preparation and photoluminescent investigation of h-BN-like layered material B4CN4. <i>Journal of Crystal Growth</i> , 2008 , 310, 3869-3872	1.6	6
11	Specific phase modulation and infrared photon confinement in solar selective absorbers. <i>Applied Materials Today</i> , 2020 , 18, 100533	6.6	6
10	Ternary compound B4CN4 prepared by direct nitridation of B4C. <i>Journal of Alloys and Compounds</i> , 2008 , 466, 299-303	5.7	5
9	Coexistence of two types of metal filaments in oxide memristors. <i>AIP Advances</i> , 2017 , 7, 025102	1.5	4
8	Aqueous solution-processed, self-flattening AlOx:Y dielectrics for fully-transparent thin-film transistors. <i>Ceramics International</i> , 2019 , 45, 15883-15891	5.1	4
7	Proton conducting sodium-alginate-gated oxide thin-film transistors with varying device structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 3103-3109	1.6	4
6	Structural and Electrochromic Properties of Undoped and Mo-Doped V2O5 Thin Films by a Two-Electrode Electrodeposition. <i>Journal of Nanoscience and Nanotechnology</i> , 2018 , 18, 7502-7507	1.3	3
5	Advances in Resistive Switching Memories Based on Graphene Oxide 2013 ,		2

- 4 Emerging Artificial Neuron Devices for Probabilistic Computing. *Frontiers in Neuroscience*, **2021**, 15, 717947 2
- 3 Optoelectronic Neuromorphic Computing: All-Optically Controlled Memristor for Optoelectronic Neuromorphic Computing (Adv. Funct. Mater. 4/2021). *Advanced Functional Materials*, **2021**, 31, 2170027^{15.6} 1
- 2 Low-Temperature Synthesis of MicroMesoporous TiO₂/SiO₂ Composite Film Containing Fe³⁺ Co-Doped Anatase Nanocrystals for Photocatalytic NO Removal. *Catalysis Letters*, **2021**, 151, 2396 2.8 0
- 1 The same batch enabled threshold voltage tuning for vertically- or laterally-gated transparent InZnO thin-film transistors. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1600918⁶ 1